

2SK360

Silicon N-Channel MOS FET

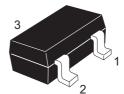
REJ03G0811-0200 (Previous ADE-208-1170) Rev.2.00 Aug.10.2005

Application

VHF amplifier

Outline

RENESAS Package code: PLSP0003ZB-A (Package name: MPAK)



- 1. Gate 2. Drain
- 3. Source



Absolute Maximum Ratings

			(Ta = 25°C)
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSX} * ¹	20	V
Gate to source voltage	V _{GSS}	±5	V
Drain current	ID	30	mA
Gate current	l _G	±1	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $V_{GS} = -4 V$

Electrical Characteristics

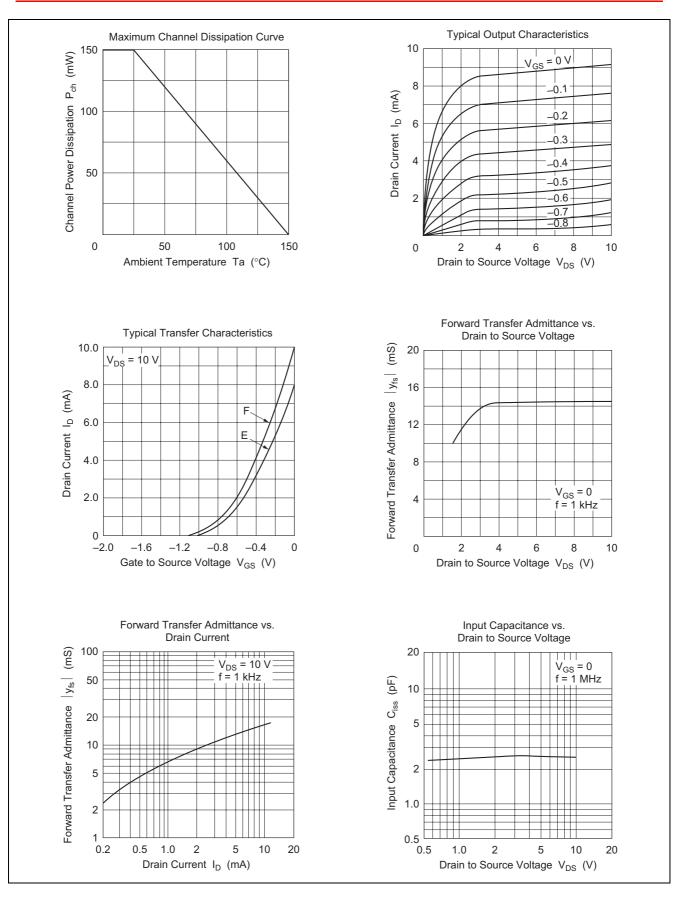
 $(Ta = 25^{\circ}C)$

ltem	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	V _{(BR)DSX}	20	—		V	$I_D = 100 \ \mu A, V_{GS} = -4 \ V$	
Gate cutoff current	I _{GSS}	_	—	±20	nA	$V_{GS} = \pm 5 V, V_{DS} = 0$	
Drain current	I _{DSS} * ¹	6	—	12	mA	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0$	
Gate to source cutoff voltage	V _{GS(off)}	0	—	-2.0	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 10 \mu\text{A}$	
Forward transfer admittance	y _{fs}	8	14	_	mS	$V_{DS} = 10 V, V_{GS} = 0,$	
						f = 1 kHz	
Input capacitance	Ciss	_	2.5	_	pF	$V_{DS} = 10 V, V_{GS} = 0,$	
Output capacitance	Coss	_	1.6	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss		0.03		pF]	
Power gain	PG		30		dB	$V_{DS} = 10 V, V_{GS} = 0,$	
Noise figure	NF	_	2.0	_	dB	f = 100 MHz	

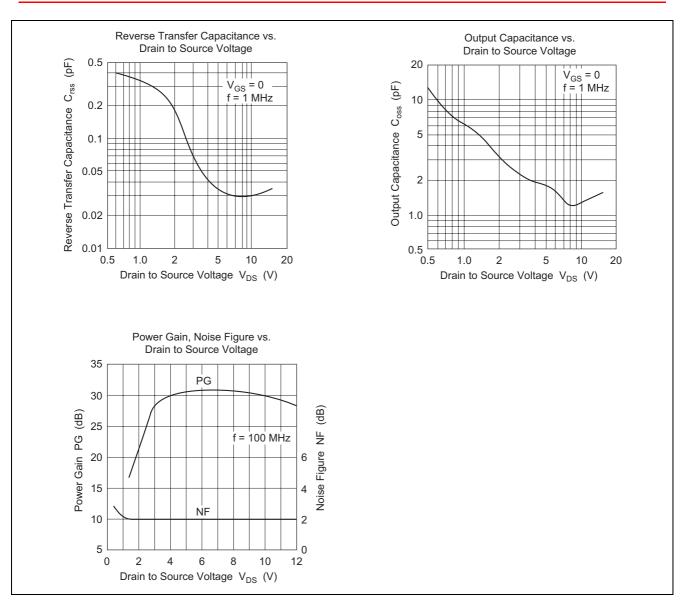
Note: 1. The 2SK360 is grouped by I_{DSS} as follows.

Grade	E	F
Mark	IGE	IGF
I _{DSS}	6 to 10	8 to 12



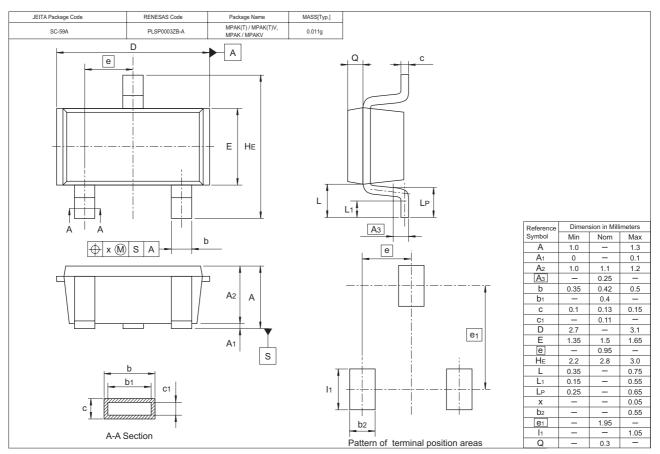








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK360IGETL	3000	φ178mm Reel , 8mm Emboss Taping
2SK360IGFTL	3000	φ178mm Reel , 8mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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